

IN THE CLAIMS:

1. (Currently Amended) A semiconductor component, ~~wherein the component comprises an electroconductive~~comprising a semiconductor element and an electroconductive element ~~provided with~~comprising at least one outlet, ~~so that the wherein the at least one outlet is configured to connect the electroconductive element is groundable via an outlet for shielding to ground in order to shield the semiconductor component~~element against electrostatic pulses.
2. (Original) A semiconductor component according to claim 1, **wherein** in structure, the electroconductive element is a planar sheet.
3. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element is a thin loop structure.
4. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element forms a permanent, integrated part of the semiconductor component.
5. (Original) A semiconductor component according to claim 4, **wherein** the electroconductive element is placed underneath the cover element of the semiconductor component, inside said cover element.
6. (Original) A semiconductor component according to claim 4, **wherein** the electroconductive element is placed on top of the cover element of the semiconductor component, outside said cover element.
7. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.
8. (Currently Amended) A method for shielding a semiconductor ~~component~~element against electrostatic pulses, comprising: integrating an ~~electroconductive element~~the semiconductor element in the ~~semiconductive a semiconductor~~ component, integrating an electroconductive element in the

semiconductor component and providing at least one outlet for the integrated electroconductive element, so that the at least one outlet is configured to connect the electroconductive element is groundable through the outlet to ground.

9. (Original) A method according to claim 8, **wherein** in the semiconductor component, there is integrated an electroconductive, planar element.
10. (Original) A method according to claim 8, **wherein** in the semiconductor component, there is integrated an electroconductive, loop-shaped element.
11. (Previously Presented) A method according to claim 8, **wherein** the electroconductive element is integrated as a permanent part of the semiconductor component.
12. (Original) A method according to claim 11, **wherein** the electroconductive element is integrated underneath the cover element of the semiconductor component, inside said cover element.
13. (Original) A method according to claim 11, **wherein** the electroconductive element is integrated on top of the cover element of the semiconductor component, outside said cover element.
14. (Original) A method according to claim 8, **wherein** the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.
15. (Currently Amended) An apparatus arrangement including a mounting tray and components, ~~wherein a component of the components comprises a~~ at least one semiconductor component, in which there is ~~wherein said at least one semiconductor component comprises a semiconductor element and an~~ integrated an electroconductive element, ~~and where the electroconductive element is provided with at least one outlet that is grounded to a ground plane of the mounting tray.~~
16. (Currently Amended) Apparatus for shielding a semiconductor ~~component~~ element against electrostatic pulses, comprising:

means for integrating ~~an electroconductive element~~the semiconductor element
~~in the semiconductor~~a semiconductor component; and

means for integrating an electroconductive element in the semiconductor component and for providing at least one outlet for the integrated electroconductive element, so that the at least one outlet is configured to connect the electroconductive element~~is groundable through the outlet to ground.~~

17. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, planar element.

18. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped element.

19. (Previously Presented) The apparatus of claim 16, wherein the electroconductive element is integrated as a permanent part of the semiconductor component.

20. (Previously Presented) The apparatus of claim 16, wherein the electroconductive element is integrated underneath the cover element of the semiconductor component, inside said cover element.